



Attorney Docket No. P120-US

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of: Hongqin Shi, et al.

Art Unit: Not Yet Assigned

Serial No.: 10/666,002

Examiner: Not Yet Assigned

Filed: 9/17/03

For: **AN ETCHING METHOD USED IN FABRICATIONS OF MICROSTRUCTURES**

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 CFR 1.97(b)**

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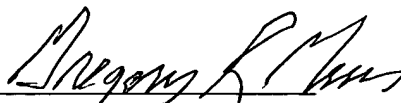
The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO Form 1449. Copies of the cited references are enclosed.

No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the last of (1) issuance of a first official action on the merits and (2) expiration of the three month period following filing of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can determine any materiality thereof to the claimed invention. It is respectfully requested that the information be considered during the prosecution of this application and that the cited documents be listed on the front page of any patent issuing from this application.

The Patent Office is authorized to charge our Deposit Account No. 501516 for any fee which it deems to be required to effect consideration of this statement.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Gregory R. Muir", written over a horizontal line.

Gregory R. Muir  
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		Application Number	10/666,002		
		Filing Date	9/17/03		
		First Named Inventor	Shi		
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		Examiner Name	Not Yet Assigned		
Sheet	1	of	6	Attorney Docket Number	P120-US

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
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		US- 6,051,503	04-18-2000	Bhardwai, J.K.	
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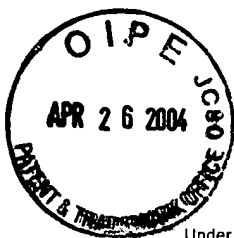
FOREIGN PATENT DOCUMENTS						
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		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
		EP-0704884-A2	04-03-1996	Mehta, J.		
		EP-0822582-A2	02-04-1998	Bhardwai, J.K.		
		EP-0822584-A2	04-04-1998	Bhardwai, J.K.		
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		JP-1985/60057938-A	04-03-1985	Katsumi et al.		
		WO-98/32163	07-23-1998	Tai et al.		

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		Number - Kind Code <sup>2</sup> (if known)			
		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
		US- 6,396,619 B1	05-28-2002	Huibers, et al.	
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		US- 2003/0124848 A1	0703/03	Chinn, et al.	
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		Country Code <sup>3</sup> -Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
		JP-1997/09251981-A	09-22-1997	Kazuaki et al.		
		JP-1998/10313128-A	11-24-1998	Hanmin et al.		
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		JP-1986/61134019-A	06-21-1986	Shinii et al.		
		JP-1986/61181131-A	08-13-1986	Shinii et al.		

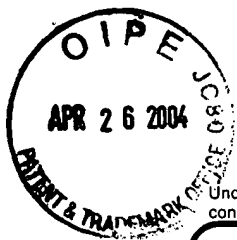
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				<b>Application Number</b>	10/666.002	
<b>Sheet</b>		<b>4</b>	<b>of</b>	<b>6</b>	<b>Filing Date</b>	9/17/03
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					<b>Group Art Unit</b>	Not Yet Assigned
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<b>OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS</b>			
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		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F2 and XeF2 Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
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		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
		WINTERS et al., "The Etching of Silicon with XeF <sub>2</sub> Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
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		"Xenon Difluoride Isotropic Etch System: Seeing is Believing", Surface Technology Systems Ltd. brochure, Newport, UK (date unknown).	
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		BASSOM et al., "Modeling and Optimizing XeF <sub>2</sub> -enhanced FIB Milling of Silicon", 25th International Symposium for Testing and Failure Analysis, Santa Clara, CA (Nov. 14 -18, 1999), pp. 255-261 (abstract only).	
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		CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	

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		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF <sub>2</sub> Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
		SEBEL et al., "Silicon Etch Rate Enhancement by Traces of Metal", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 3, (May/June 1999), pp. 755-762 (abstract only).	
		SUGANO et al., "Study on XeF <sub>2</sub> Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Micromechanics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
		WANG et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 2 (June 16 - 19, 1997), pp. 1505-1508 (abstract only).	
		MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the Mitel 1.5- $\mu$ m CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
		TODA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 671-674.	
		SEBEL et al., "Etching of Si Through a Thick Condensed XeF <sub>2</sub> Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

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